

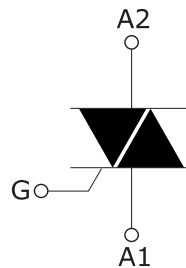
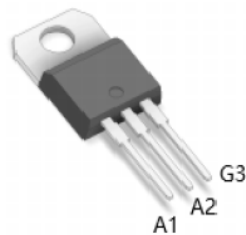
1.Description

NPNN five-layer structure of silicon bidirectional devices; with independent intellectual property rights of single-sided digging technology, table glass passivation process; multi-layer metallized electrodes on the back; with high blocking voltage and high temperature stability.

2.Features

vacuum cleaners, power tools and other motor speed controllers; solid state relays; heating controllers (temperature regulation); other phase control circuits.

3.Pinning Information



TO-220A



4. Absolute maximum ratings ($T_J=25^{\circ}\text{C}$ unless otherwise stated)

Parameter			Symbol	Values	Units
RMS on-state current (full sine wave)	BTA	T _C =80°C	I _{T(RMS)}	12	A
Non repetitive surge peak on-state current (full cycle, T _J initial=25°C)	F=50HZ, tp=20ms		I _{TSM}	120	A
I ² t value for fusing	tp=10ms		I ² t	72	A ² S
Critical rate of rise of on-state current I _G =2 x I _{GT} , tr≤100ns	T _J =125		di/dt	50	A/us
Off state repetitive peak voltage Reverse repetitive peak voltage	T _J =25°C		V _{DRM} /V _{RRM}	600/800	V
Peak gate current	tp=20us	T _J =150°C	I _{GM}	4	A
Average gate power dissipation		T _J =150°C	P _{G(AV)}	1	W
Storage junction temperature range			T _{STG}	-40 to 150	°C
Operating junction temperature range			T _J	-40 to 125	°C



5.1 Electrical characteristics (3 quadrants)

Parameter	Quadrant	Range	Symbol	Values				Units
$V_D=12V$ $R_L=100\Omega$	I	MAX	I_{GT}	BW	CW	SW	TW	mA
		MAX		50	35	10	5	mA
$V_D=V_{DRM}$, $R_L=3.3k\Omega$, $T_J=125^\circ C$	II	MAX	V_{GT}	1.5				V
	III	MIN	V_{GD}	0.2				V
$I_T=100mA$		MAX	I_H	60	40	20	15	mA
$I_G=1.2 \times I_{GT}$		MAX	I_L	100	60	40	30	mA
$V_D = 67\% V_{DRM}$, gate open, mA, $T_J=125^\circ C$		MIN	dv/dt	500	500	200	100	V/us
Critical rise rate of commutation voltage $T_J=150^\circ C$		MIN	(dv/dt) _c	8				V/us

5.2 Electrical characteristics (4 quadrants)

Parameter	Quadrant	Range	Symbol	Values		Units
				B	C	
$V_D=12V$ $R_L=100\Omega$	I - II - III	MAX	I_{GT}	50	20	mA
	IV	MAX		100	60	mA
	ALL	MAX	V_{GT}	1.5		V
$V_D=V_{DRM}$, $R_L=3.3k\Omega$, $T_J=125^\circ C$	ALL	MIN	V_{GD}	0.2		V
$I_T=500mA$		MAX	I_H	60	50	mA
$I_G=1.2 \times I_{GT}$	I - II - III	MAX	I_L	60	50	mA
	IV	MAX		100	80	mA
$V_D = 67\% V_{DRM}$, gate open, mA, $T_J=125^\circ C$		MIN	dv/dt	500		V/us
Critical rise rate of commutation voltage $T_J=150^\circ C$		MIN	(dv/dt) _c	10		V/us



6.Static Parameters

Parameter			Symbol	Values	Units
$I_{TM}=24A$	$T_J=25^{\circ}C$	MAX	V_{TM}	1.5	V
threshold on-state voltage	$T_J=150^{\circ}C$	MAX	V_{T0}	0.86	V
Dynamic resistance	$T_J=150^{\circ}C$	MAX	R_d	36.6	mΩ
$V_{DRM}=V_{RRM}$	$T_J=25^{\circ}C$	MAX	I_{DRM}, I_{RRM}	5	uA
	$T_J=150^{\circ}C$	MAX		1	mA
Junction to ambient	BTA	MAX	$R_{th(j-c)}$	2.05	°C/W



7. Typical Characteristic

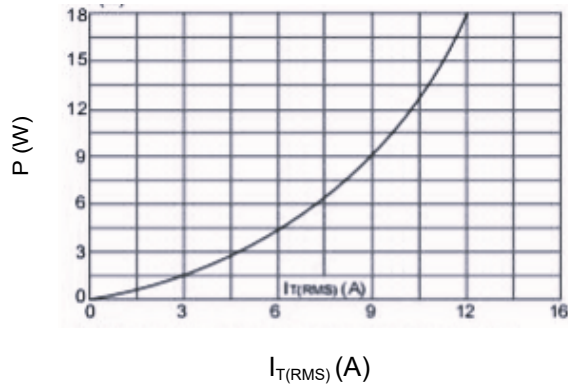


Figure 1: Maximum power dissipation versus RMS on-state current

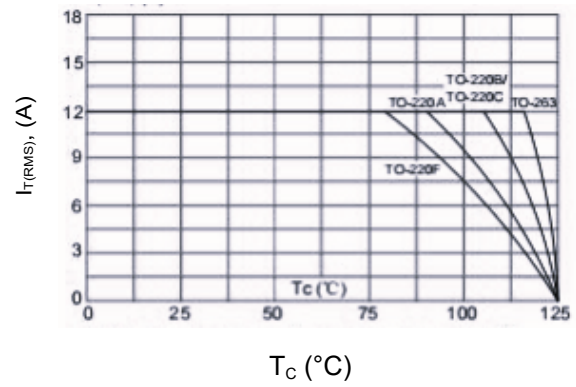


Figure 2: RMS on-state current versus case temperature

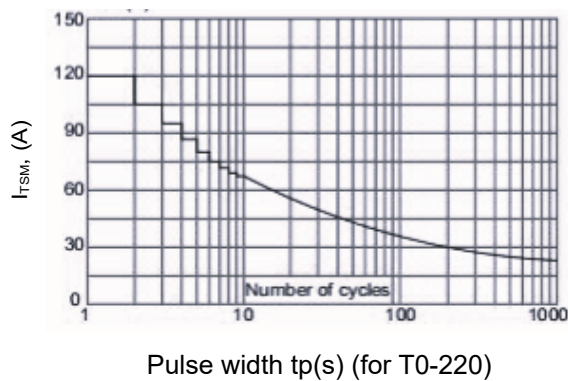


Figure 3: Surge peak on-state current versus number of cycles

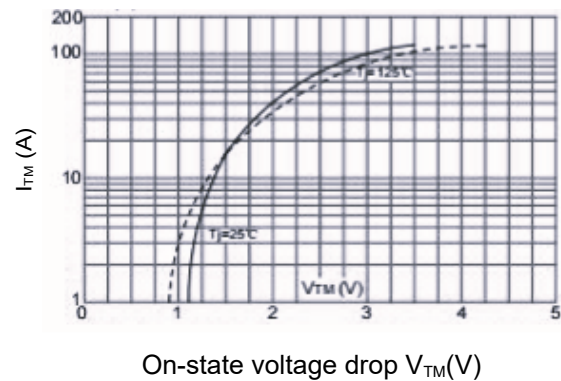


Figure 4: On-state characteristics (maximum values)

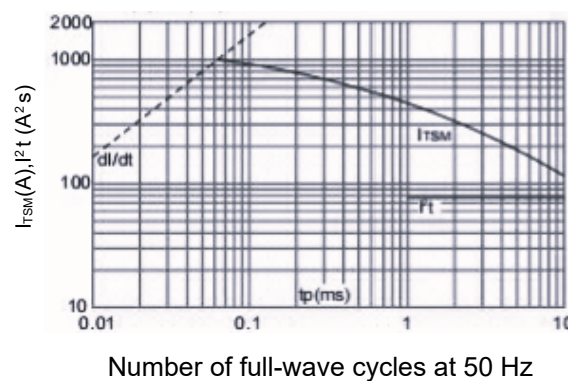


Figure 5: Non-repetitive surge peak on-state current for a sinusoidal pulse with width $t_p < 10\text{ms}$

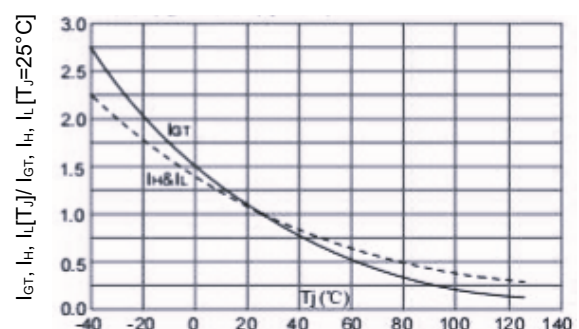
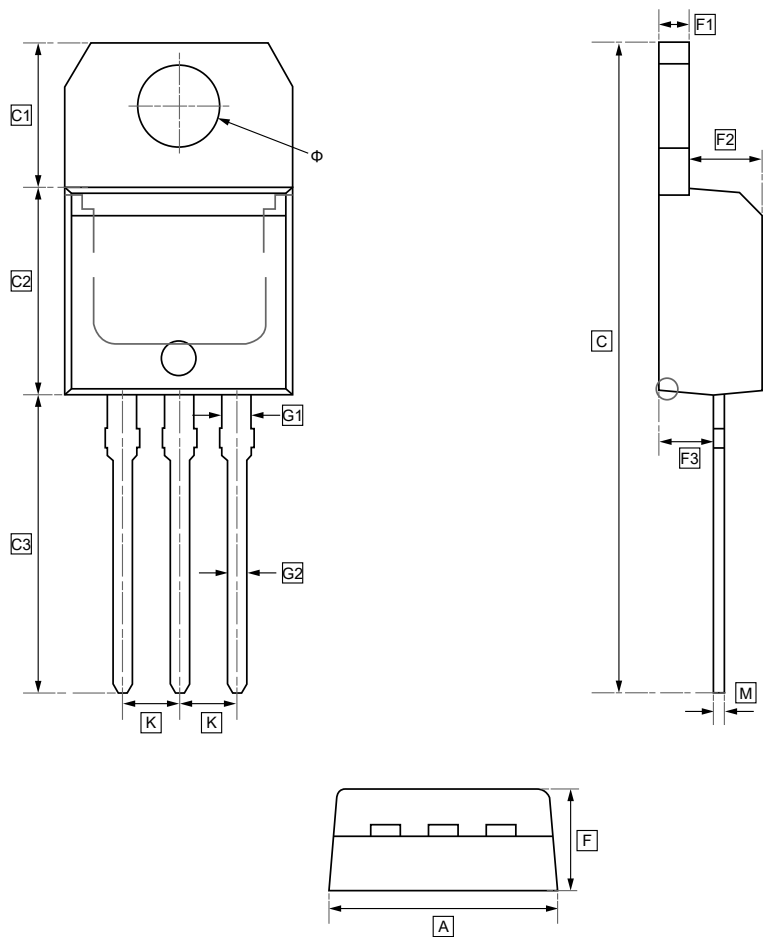


Figure 6: Relative variations of gate trigger current, holding current and latching current versus



8.TO-220 Package Outline Dimensions



DIMENSIONS (mm are the original dimensions)

Symbol	A	C	C1	C2	C3	Φ	F	F1	F2	F3	G1	G2
Min	10.000	28.700	6.400	9.040	13.160	3.700	4.350	1.220	3.130	2.300	1.220	0.750
Max	10.200	29.100	6.500	9.240	13.460	3.800	4.650	1.320	3.330	2.700	1.320	0.850

Symbol	M	K
Min	0.450	2.540
Max	0.550	



9.Ordering information

BTA12-600B
UMW yyww

yy: Year Code
ww: Week Code

Order Code	Marking	Package	Base QTY	Delivery Mode
UMW BTA12-600BRG	BTA12-600B	TO-220A	1000	Tube and box
UMW BTA12-600CRG	BTA12-600C	TO-220A	1000	Tube and box
UMW BTA12-800BRG	BTA12-800B	TO-220A	1000	Tube and box
UMW BTA12-800CRG	BTA12-800C	TO-220A	1000	Tube and box
UMW BTA12-600BWRG	BTA12-600BW	TO-220A	1000	Tube and box
UMW BTA12-600CWRG	BTA12-600CW	TO-220A	1000	Tube and box
UMW BTA12-800BWRG	BTA12-800BW	TO-220A	1000	Tube and box
UMW BTA12-800CWRG	BTA12-800CW	TO-220A	1000	Tube and box
UMW BTA12-600SWRG	BTA12-600SW	TO-220A	1000	Tube and box
UMW BTA12-600TWRG	BTA12-600TW	TO-220A	1000	Tube and box
UMW BTA12-800SWRG	BTA12-800SW	TO-220A	1000	Tube and box



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